Please type a plus sign (+) inside this box → [+]

PTO/SB/08B (08-00)
Approved for use through 10/31/2002.OMB 0651-0031
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 2

Complete if Known	
Application Number	09/851,952-4043
Filing Date	May 9, 2001
First Named Inventor	Theodore H. Fedynyshyn
Group Art Unit	1752
Examiner Name	Not Yet Assigned A. Walke
Attorney Docket Number	101328-0151

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
ACW	V	Wu-Song Huang, SPIE Conference, Polymeric Base Additives for Lithographic Improvement in DUV Resist System, SPIE Vol. 3678, pages 1040-1051, 1999.	
	W	Ferreira et al., Choice of Amines as Stabilizers for Chemically Amplified Resist Systems, SPIE Vol. 3333, Pages 236-244, 1998.	
	X	Kawai et al., Advances in Patterning Characteristics of Chemically Amplified Resists with an Organic Base, Journal of Photopolymer Science and Technology, Vol. 11, No. 3, 399-404, 1998.	
	Y	Ushirogouchi et al., Mechanism of Amine Additive in Chemically Amplified Resist Visualized by Using Monte-Carlo Simulation, SPIE Vol. 2438, Pages 609-616, 1995.	
	Z	Asakawa et al., Effect of Basic Additives on Sensitivity and Diffusion of Acid in Chemical Amplification Resists, SPIE Vol. 2438, Pages 563-570, 1995.	
	AA	Yamaguchi et al., A New Approach for Reducing Line-Edge Roughness by Using a Cross-linked Positive-tone Resist, Pages 158-159.	
	AB	Sanchez et al., Effect of Aerial Image Contrast on Resist Line-Edge Roughness, Microlithography World, Pages 19-21, 1999.	
	AC	Sanchez et al., Aerial Image Contrast Using Interferometric Lithography: Effect on Line-Edge Roughness, SPIE Volume 3678, Pages 160-171, 1999.	
	AD	Brainard et al., Comparison of the Lithographic Properties of Positive Resists Upon Exposure to Deep-and Extreme-Ultraviolet Radiation, J.Vac. Sci. Technol. B 17(6), Pages 3384-3389, 1999.	
	AE	Hinsberg et al., Factors Controlling Pattern Formation in Chemically Amplified Resists at Sub-100 nm Dimensions, J. Photopolym. Sci. Technol., Volume 12, No. 4, Pages 649-562, 1999.	
	AF	Wallow et al., Evaluation of Cycloolefin-Maleic Anhydride Alternating Copolymers as Single-Layer Photoresists for 193 nm Photolithography, SPIE Vol. 2724, Pages 355-364, 1996.	
	AG	Palmateer et al., Line Edge Roughness in sub-018-μm Resist Patterns, SPIE Volume, 634-642, 1998.	
	AH	Geoffrey W. Reynolds and James W. Taylor, Factors Contributing to Sidewall Roughness in a Positive-Tone, Chemically Amplified Resist Exposed by X-ray Lithography, J. Vac. Sci. Technol. B 17(2), Pages 334-344, 1999.	
	AI	Yamaguchi et al., A New Approach for Reducing Line-Edge Roughness by Using a Cross-Linked Positive Tone-Resist, NTT Basic Research Laboratories, Pages 158-159.	
ACW	AJ	Houlihan et al., A Commericially Viable 193 nm Single Layer Resist Platform, Journal of Photopolymer Science and Technology, Pages 511-520, 1997.	

Examiner Signature	Amanda C. Walke	Date Considered	August 1, 2002

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]Applicant is to place a check mark here if English language Translation is attached

PTO/SB/08A (08-00)
Approved for use through 10/31/2002.OMB 0651-0031
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Please type a plus sign (+) inside this box → [+]

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

Complete if Known	
Application Number	09/851,952-4043
Filing Date	May 9, 2001
First Named Inventor	Theodore H. Fedynyshyn
Group Art Unit	1752
Examiner Name	Not Yet Assigned A. Wawe
Attorney Docket Number	101328-0151

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
ACW	A	3148983		Endermann et al.	09/15/64	
	B	3869292		Peters	03/04/75	
	C	4115128		Kita	09/19/78	
	D	4246374		Kopchik	01/20/81	
	E	4377631		Toukhy et al.	03/22/83	
	F	4404272		Stahlhofen	09/13/83	
	G	4404357		Taylor et al.	09/13/83	
	H	4423138		Guild	12/27/83	
	I	4424315		Taylor et al.	01/03/84	
	J	4439516		Cernigliaro et al.	03/27/84	
	K	4491628		Ito et al.	01/01/85	
	L	4791171		Cunningham	12/13/88	
	M	4931379		Brunsvold et al.	06/05/90	
	N	4939070		Brunsvold et al.	07/03/90	
	O	5609989		Bantu et al.	03/11/97	
	P	5667938		Bantu et al.	09/16/97	
	Q	5733705		Bantu et al.	03/31/98	
	R	5879856		Thackeray et al.	03/09/99	
	S	5998099		Houlihan et al.	12/07/99	
ACW	T	6037107		Thackeray et al.	03/14/00	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Number[4]	Kind Code[5] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
ACW	U		WO 00/67072		Feiring et al.	11/09/00		

Examiner Signature	Amanda C. Wawe	Date Considered	August 1, 2002

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Unique citation designation number. [2] See attached Kinds of U.S. Patent Documents. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.